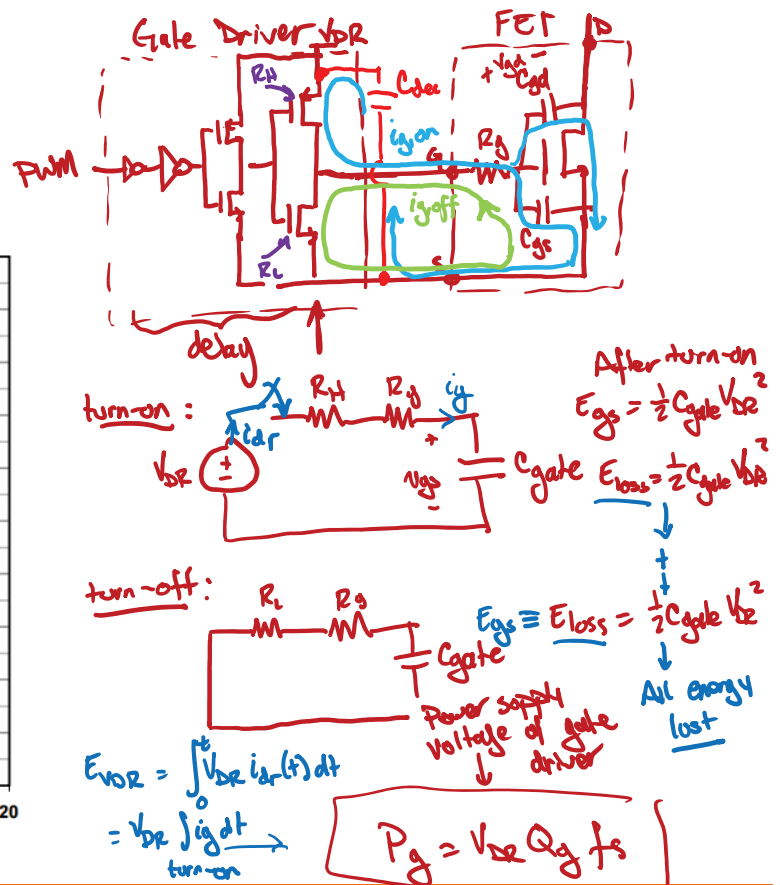
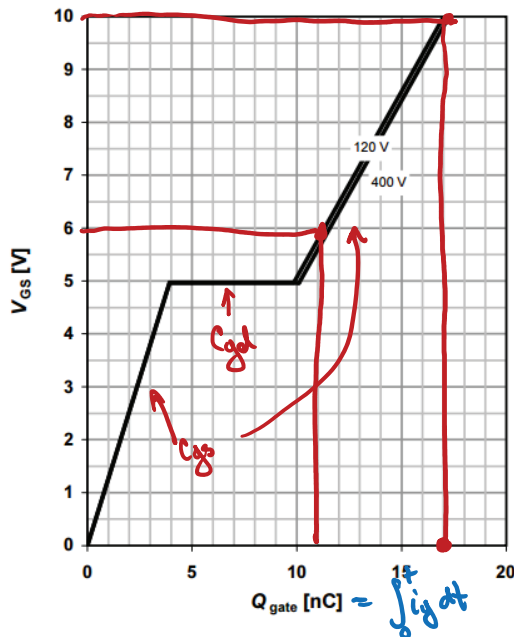


Gate Charge

9 Typ. gate charge

$$V_{GS}=f(Q_{gate}); I_D=5.2 \text{ A pulsed}$$

parameter: V_{DD}

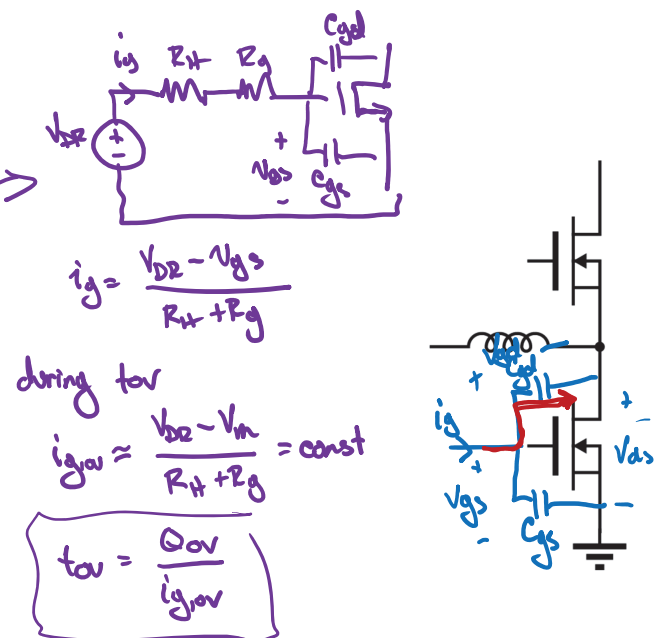
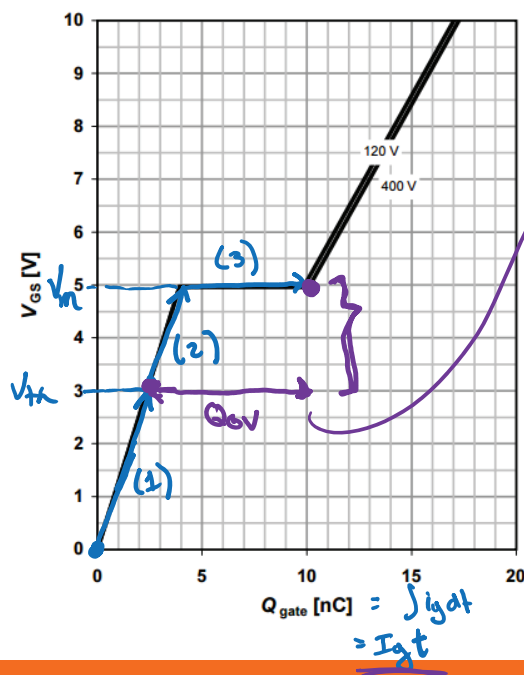


Overlap Time

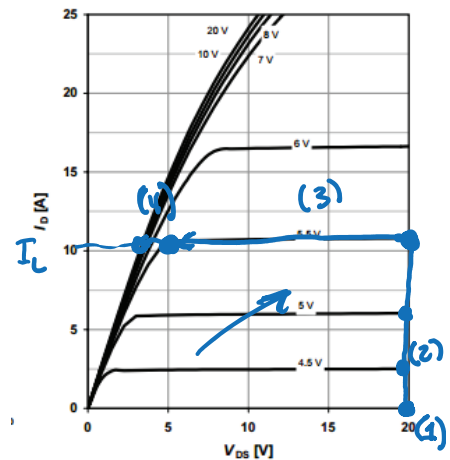
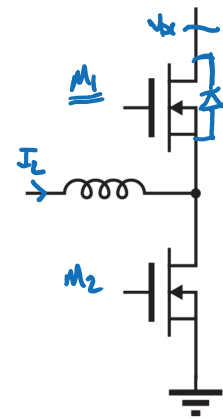
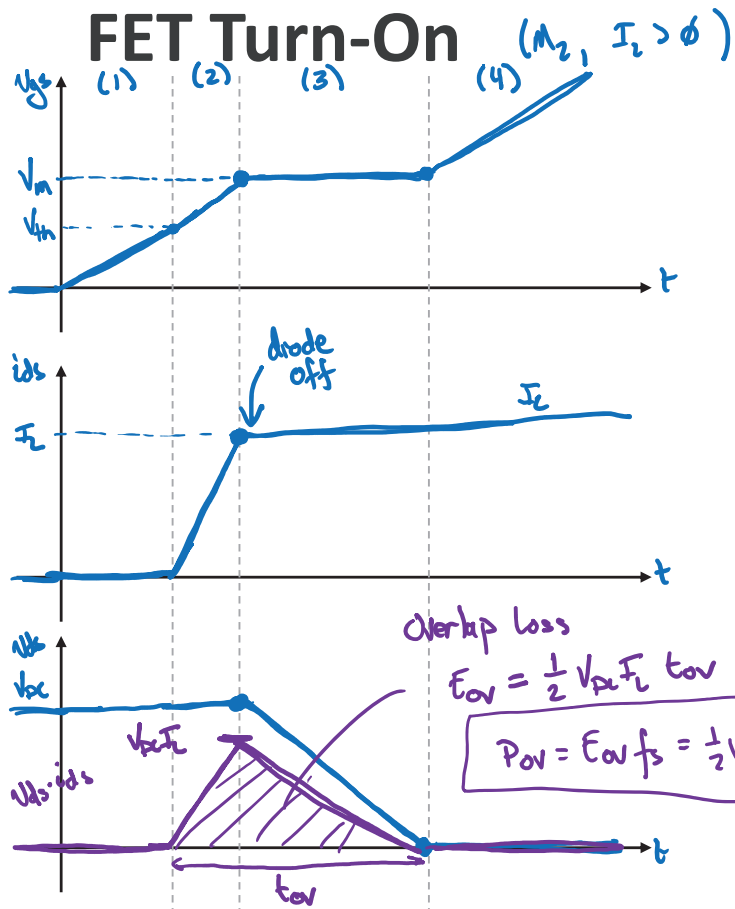
9 Typ. gate charge

$$V_{GS}=f(Q_{gate}); I_D=5.2 \text{ A pulsed}$$
parameter: V_{DD}

Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=0.34\text{ mA}$	2.5	3	3.5
Gate resistance	R_G	$f=1\text{ MHz}$, open drain	-	1.8	- Ω



FET Turn-On



Device Transconductance

$$i_{ds} \approx g_{fs} (V_{gs} - V_{th})$$

End of (2): $\frac{I_L}{g_{fs}} = V_m - V_{th}$

